

Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	768	A
	@ $T_C=65^{\circ}\text{C}$	600	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	1200	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	1875	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	650	V
I_F	Diode Continuous Forward Current	600	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	1200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	2500	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.45	1.90	V
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.60		
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		1.70		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=9.60\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.1	5.8	6.5	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			0.5		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		69.5		nF
C_{res}	Reverse Transfer Capacitance				1.37	
Q_G	Gate Charge	$V_{GE}=-15 \dots +15\text{V}$		4.16		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=600\text{A}, R_G=2.4\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		100		ns
t_r	Rise Time			90		ns
$t_{d(off)}$	Turn-Off Delay Time			536		ns
t_f	Fall Time			56		ns
E_{on}	Turn-On Switching Loss			8.90		mJ
E_{off}	Turn-Off Switching Loss			17.2		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=600\text{A}, R_G=2.4\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		110		ns
t_r	Rise Time			95		ns
$t_{d(off)}$	Turn-Off Delay Time			568		ns
t_f	Fall Time			60		ns
E_{on}	Turn-On Switching Loss			9.90		mJ
E_{off}	Turn-Off Switching Loss			20.0		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=600\text{A}, R_G=2.4\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$		120		ns
t_r	Rise Time			100		ns
$t_{d(off)}$	Turn-Off Delay Time			584		ns
t_f	Fall Time			60		ns
E_{on}	Turn-On Switching Loss			10.5		mJ
E_{off}	Turn-Off Switching Loss			21.2		mJ
I_{SC}	SC Data	$t_p \leq 6\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=360\text{V}, V_{CEM} \leq 650\text{V}$		3000		A

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit		
V_F	Diode Forward Voltage	$I_C=600\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.55	2.00	V		
		$I_C=600\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.50				
		$I_C=600\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.45				
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=600\text{A},$ $-di/dt=6000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		17.0		μC		
I_{RM}	Peak Reverse Recovery Current			205		A		
E_{rec}	Reverse Recovery Energy			4.00		mJ		
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=600\text{A},$ $-di/dt=6000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		36.0		μC		
			I_{RM}	Peak Reverse Recovery Current		300		A
			E_{rec}	Reverse Recovery Energy		9.30		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=600\text{A},$ $-di/dt=6000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		42.0		μC		
			I_{RM}	Peak Reverse Recovery Current		330		A
			E_{rec}	Reverse Recovery Energy		10.5		mJ

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.080	K/W
	Junction-to-Case (per Diode)			0.150	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.031		K/W
	Case-to-Heatsink (per Diode)		0.058		
	Case-to-Heatsink (per Module)		0.010		
M	Terminal Connection Torque, Screw M6	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

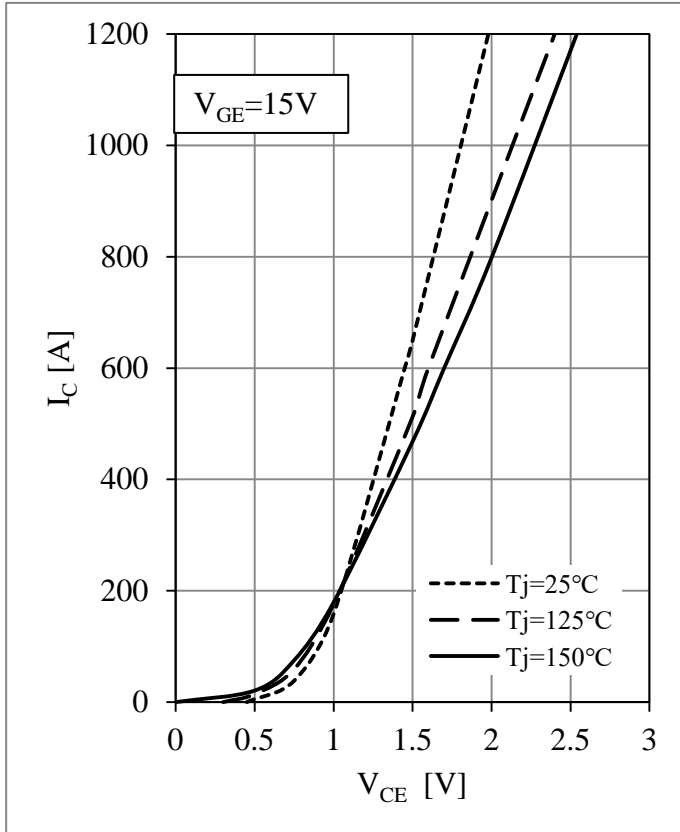


Fig 1. IGBT Output Characteristics

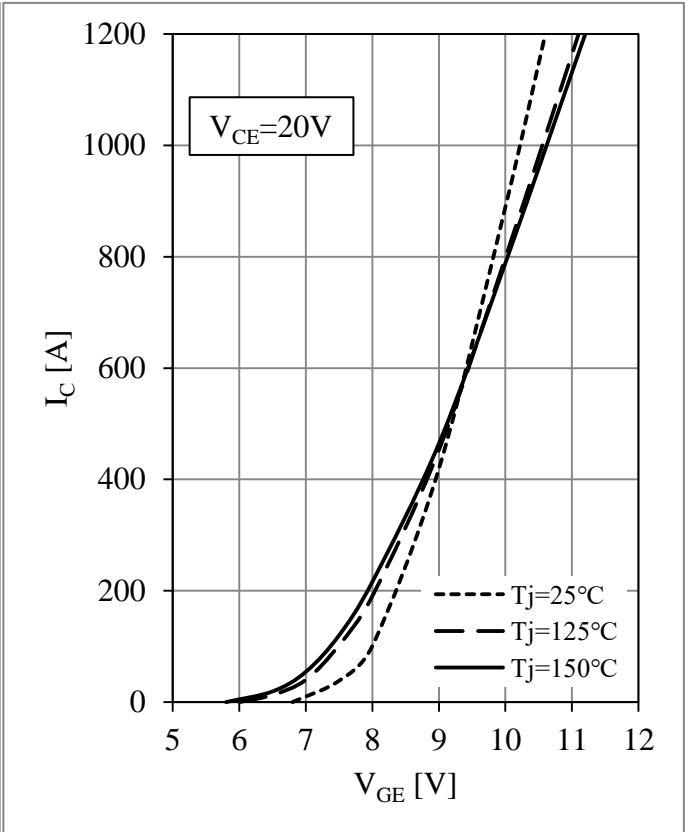


Fig 2. IGBT Transfer Characteristics

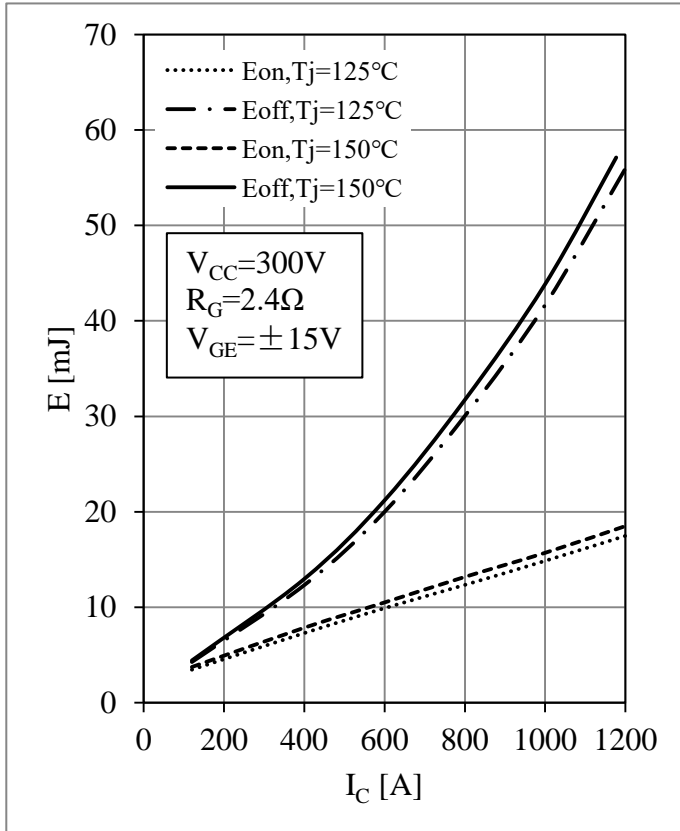


Fig 3. IGBT Switching Loss vs. I_C

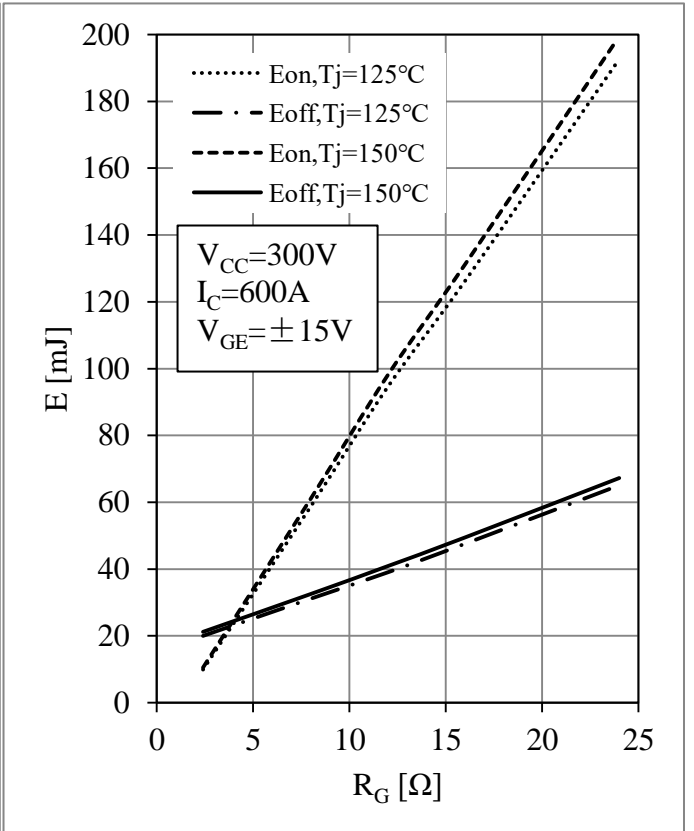


Fig 4. IGBT Switching Loss vs. R_G

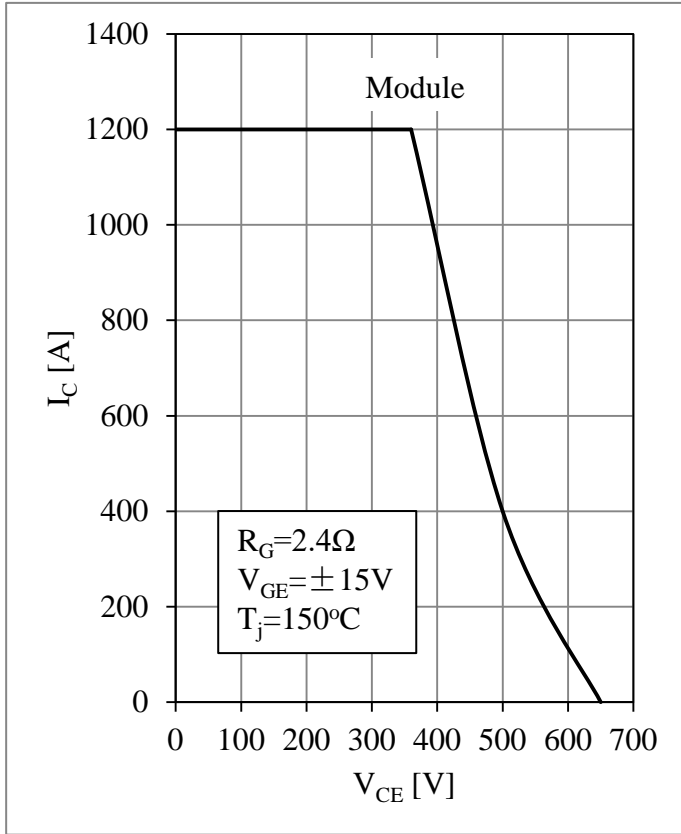


Fig 5. RBSOA

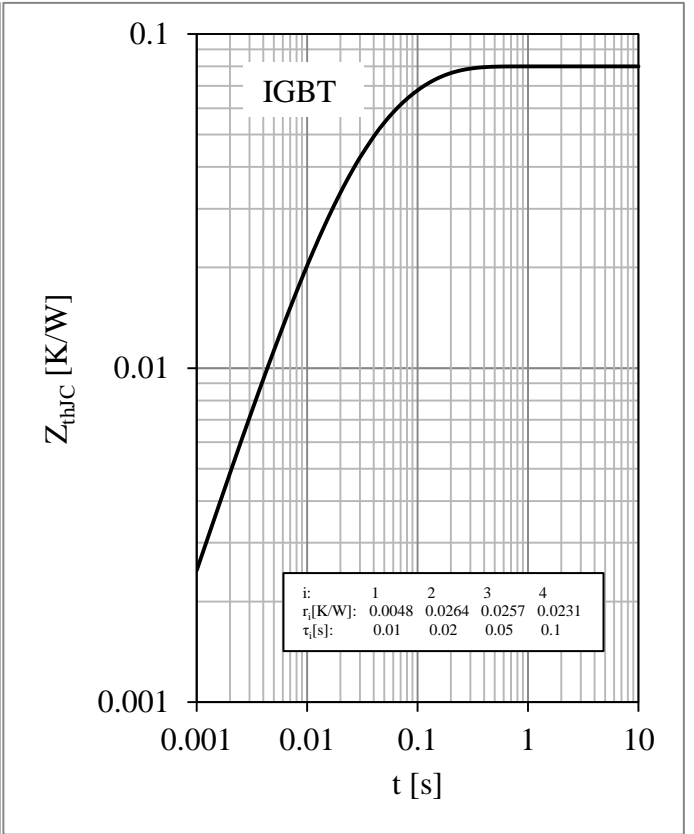


Fig 6. IGBT Transient Thermal Impedance

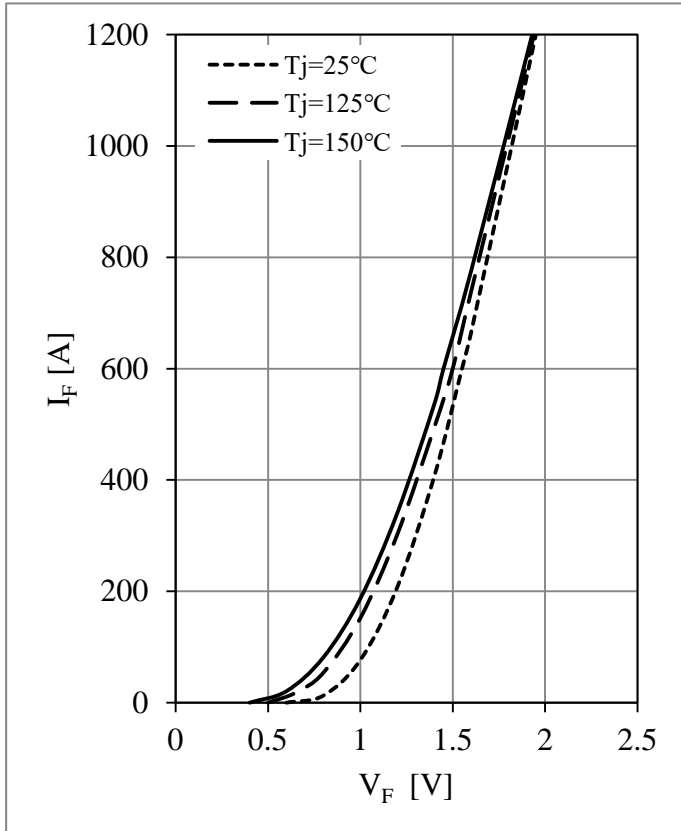


Fig 7. Diode Forward Characteristics

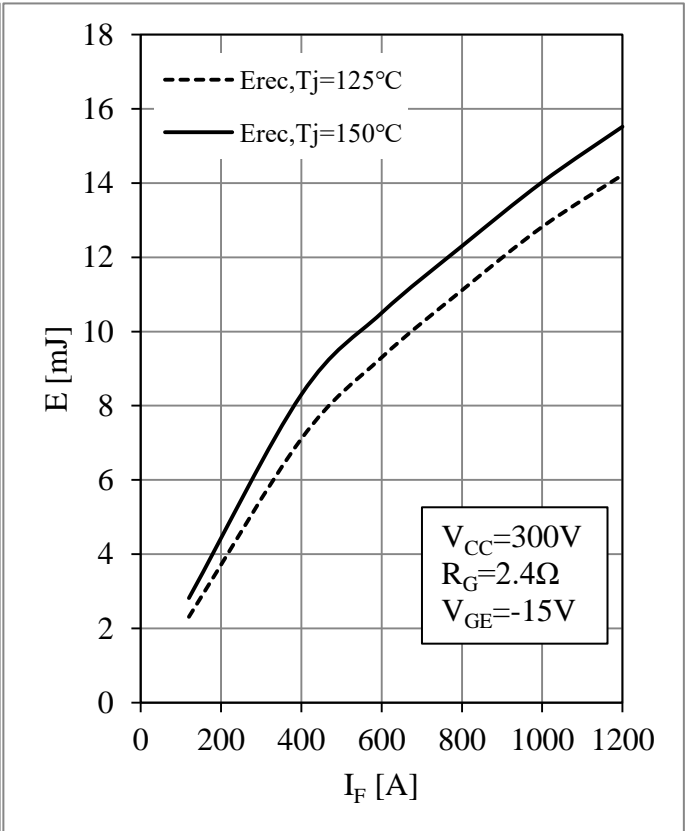


Fig 8. Diode Switching Loss vs. I_F

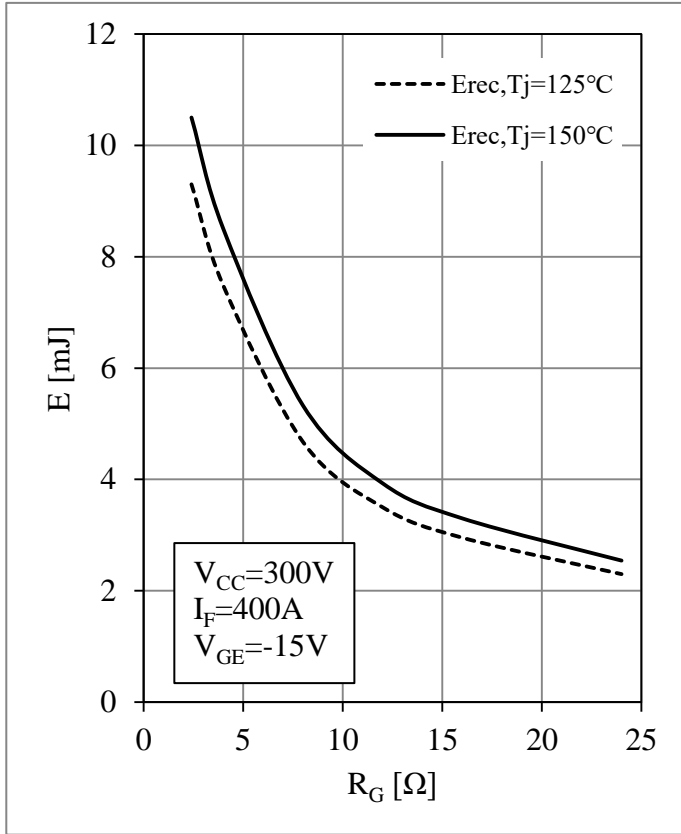


Fig 9. Diode Switching Loss vs. R_G

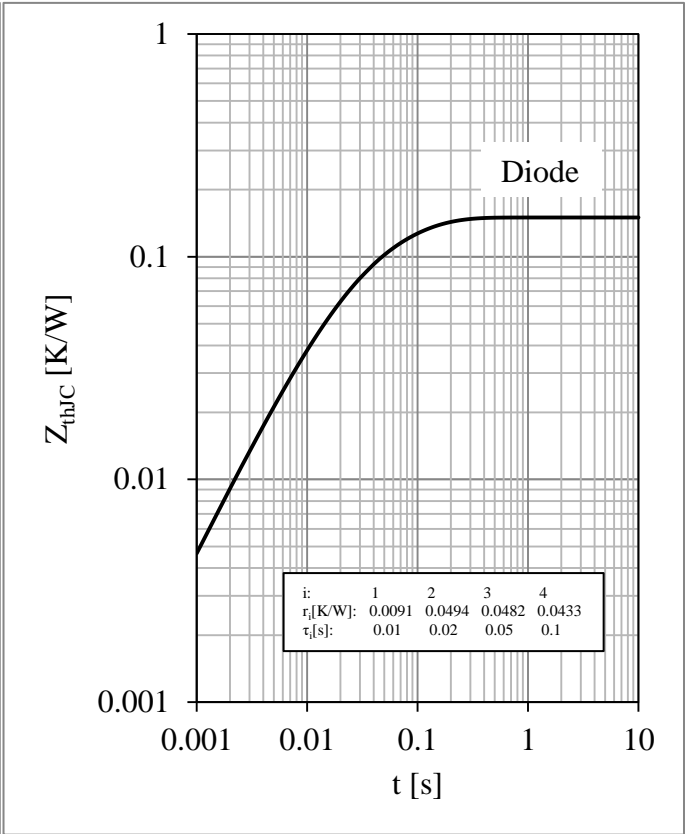


Fig 10. Diode Transient Thermal Impedance

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